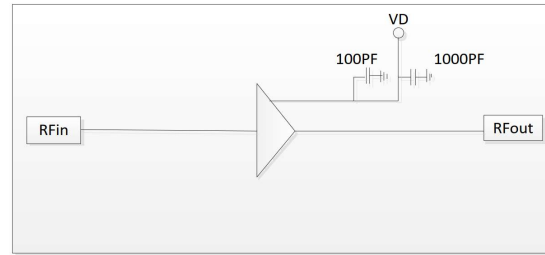


Performance

- Frequency: 8~12GHz
- Typical Signal Gain: 25dB
- Typical Pout: 27dBm
- Typical PAE: 15%
- Bias: 28V, 0.18A (Typ.)
- Technology: 0.25um HEMT
- Size: 18.03*8.7mm*2.5mm

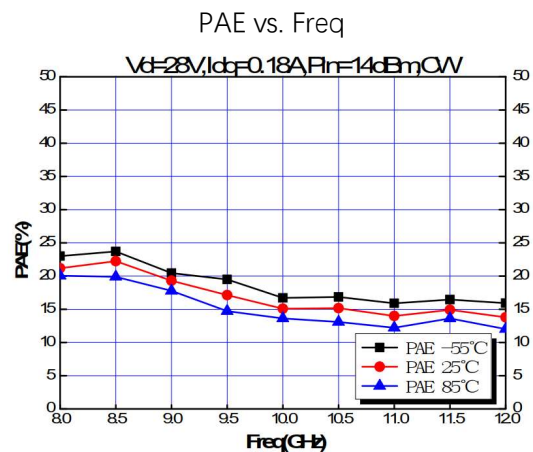
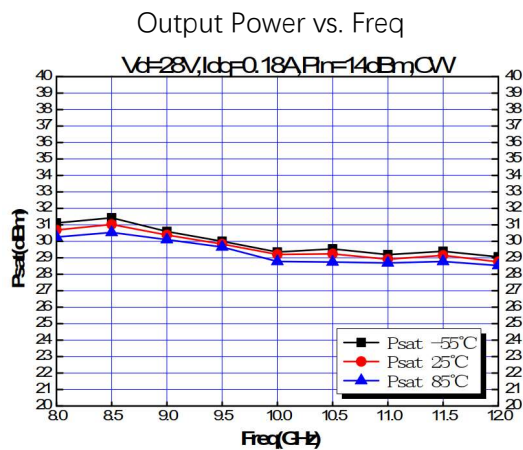
Function Diagram



Electrical Specifications (TA=25°C, Vd=28V, Idq=0.18A, F: 8~12GHz)

Symbol	Parameter	Min	Typical	Max	Unit
G	Small Signal Gain		25		dB
Gp	Power Gain (Pin=6dBm)		21		dB
Pout	Saturated Power (Pin=6dBm)		27		dBm
PAE	Power Added Efficiency (Pin=6dBm)		15		%

Test Curves (TA=25°C, F=7.5~12.5GHz)

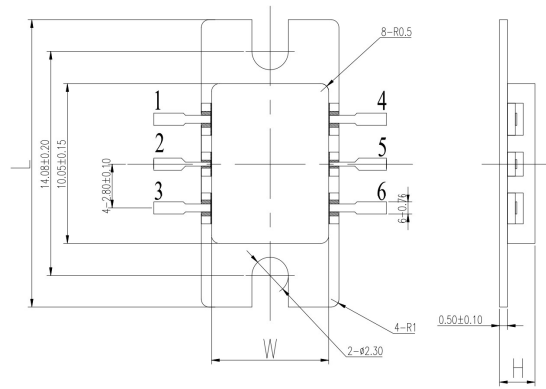


Absolute Max Ratings (TA=25°C)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	32V	
Vg	Grid Voltage	-10V	
Ig	Grid Current	10mA	
Pin	Input Power	25dBm	
VSWRout	Output VSWR	5:1	
Operating Temp.	Operating Temperature	220°C	
Tstg	Storage Temperature	-55~125°C	
ESD Sensitivity	Static Protection Grade	Class A	

Exceeding any one or combination of these limits may cause permanent damage.

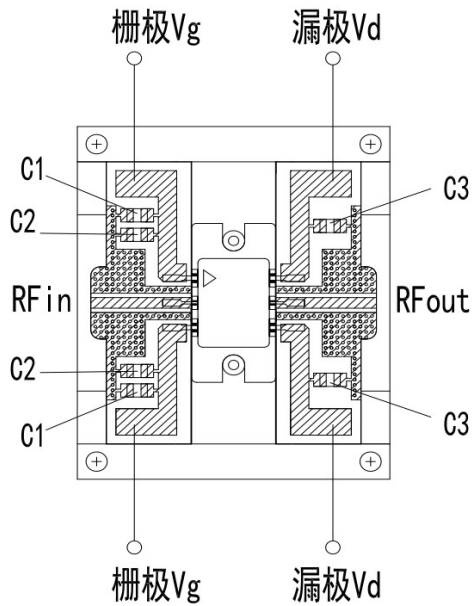
Outline Drawing



Symbol	Value		
	Min	Typ.	Max
H	-	2.24	2.50
L	17.83	18.03	18.23
W	8.50	8.70	8.90

No	Function	No	Function
1	Empty	4	Vd
2	RFin	5	RFout
3	Empty	6	Empty

Assembly Drawing



No	Recommend Capacitance
C1	10uF
C2	1uF
C3	1000pF